

Rev.03 - 21 December 2023

**Product data sheet** 

#### 1. General description

Planar passivated high commutation three quadrant triac in a TO263 (D2PAK) surface mountable plastic package. This "series E" triac balances the requirements of commutation performance and gate sensitivity. The "sensitive gate" "series E" is intended for interfacing with low power drivers including microcontrollers.

#### 2. Features and benefits

- 3Q technology for improved noise immunity
- · Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with sensitive gate
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate for easy logic level triggering
- Surface mountable package
- Triggering in three quadrants only

### **3. Applications**

- Electronic thermostats (heating and cooling)
- High power motor controls e.g. washing machines and vacuum cleaners

### 4. Quick reference data

Table 1. Q	uick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{DRM}}$	repetitive peak off-state voltage		-	-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 100 °C; <u>Fig. 1; Fig. 2; Fig. 3</u>	-	-	12	A
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 20 ms; <u>Fig 4; Fig 5</u>	-	-	100	A
		full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 16.7 ms	-	-	110	А
Tj	junction temperature		-	-	125	°C
Static ch	aracteristics					
I <sub>GT</sub>	gate trigger current	$V_{D} = 12 \text{ V}; \text{ I}_{T} = 0.1 \text{ A}; \text{ T2+ G+};$ $\text{T}_{j} = 25 \text{ °C}; \text{ Fig. 7}$	2	-	10	mA

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	2	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	2	-	10	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	15	mA
V <sub>T</sub>	on-state voltage	$I_{T} = 15 \text{ A}; T_{j} = 25 \text{ °C}; Fig. 10$	-	1.3	1.6	V
Dynamic	characteristics	·				
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit	50	-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating curren	$V_D = 400 \text{ V}; \text{ T}_j = 125 \text{ °C}; \text{ I}_{T(RMS)} = 12 \text{ A};$ $dV_{com}/dt = 20 \text{ V}/\mu \text{s}; \text{ (snubberless condition); gate open circuit}$	3	-	-	A/ms
		$V_{D}$ = 400 V; T <sub>j</sub> = 125 °C; I <sub>T(RMS)</sub> = 12 A; dV <sub>com</sub> /dt = 10 V/µs; gate open circuit	6	-	-	A/ms
		$V_{D}$ = 400 V; T <sub>j</sub> = 125 °C; I <sub>T(RMS)</sub> = 12 A; dV <sub>com</sub> /dt = 1 V/µs; gate open circuit	10	-	-	A/ms

# **5. Pinning information**

Table 2. Pi	Table 2. Pinning information								
Pin	Symbol	Description	Simplified outline	Graphic symbol					
1	T1	main terminal 1		NI					
2	T2	main terminal 2							
3	G	gate		sym051					
mb	T2	mounting base; main terminal 2							

# 6. Ordering information

Table 3. Ordering information									
Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date			
BTA312B-800E	TO263	BTA312B-800E,118	Reel	800	TO263N (N)	26-Sep-2016			
					TO263P (P)	12-Jun-2023			

### 7. Marking

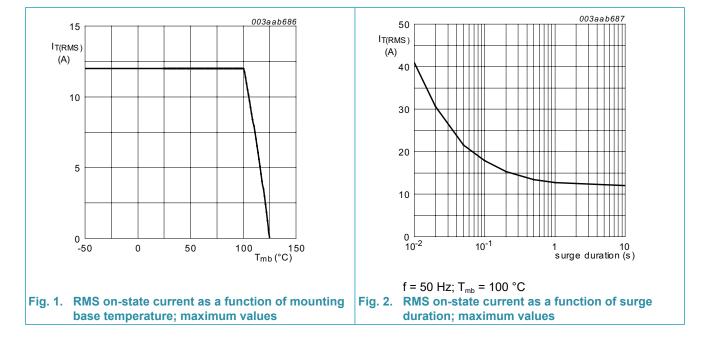
#### Table 4. Marking codes

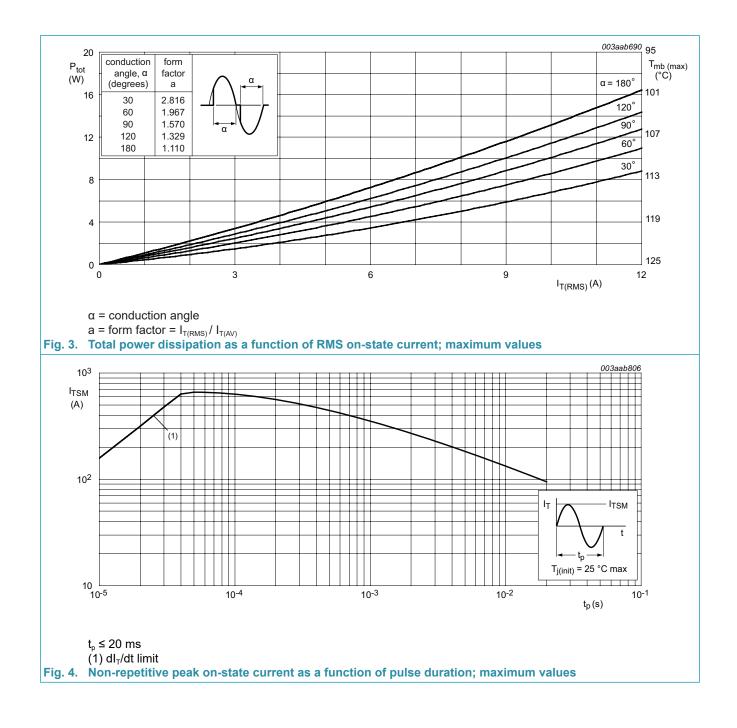
Type number	Marking codes			
	Assembly factory: N	Assembly factory: P		
BTA312B-800E	BTA312B 800E PJNxxxx xx	BTA312B 800E PJPxxxx xx		

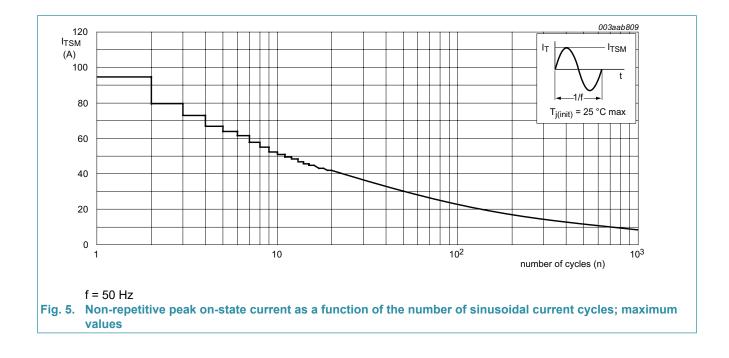
# 8. Limiting values

#### Table 5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{\text{DRM}}$	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 100 °C; <u>Fig. 1; Fig. 2; Fig. 3</u>	-	12	A
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 20 ms; <u>Fig 4; Fig 5</u>	-	100	A
		full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 16.7 ms	-	110	А
l <sup>2</sup> t	l <sup>2</sup> t for fusing	t <sub>P</sub> = 10 ms; SIN	-	50	A <sup>2</sup> s
dl <sub>⊤</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 20 mA	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	А
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

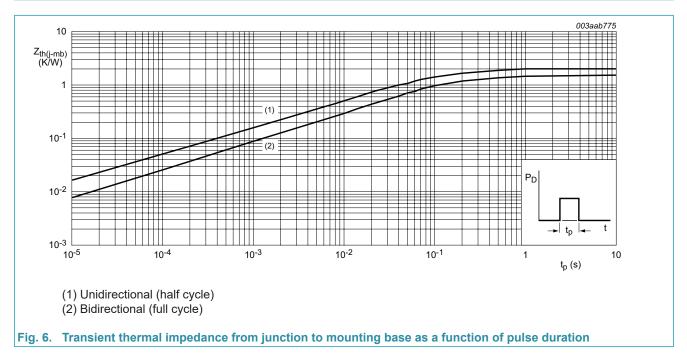






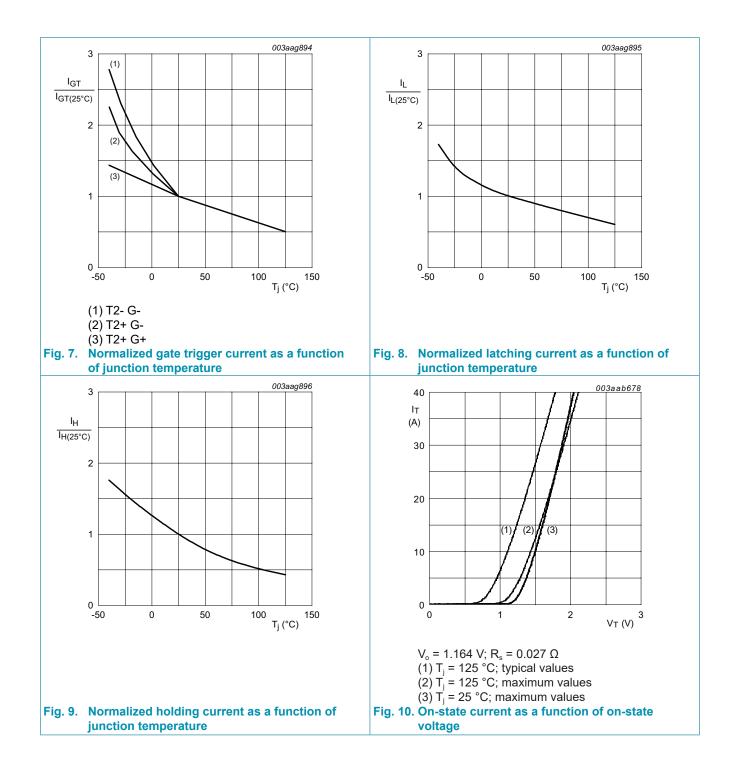
## 9. Thermal characteristics

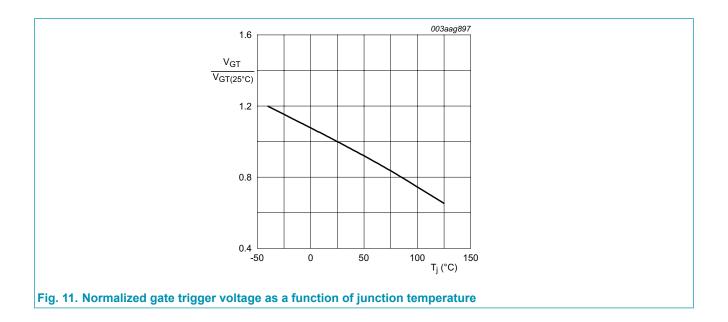
Table 6. Th	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance	full cycle; <u>Fig 6</u>	-	-	1.5	K/W
	from junction to mounting base	half cycle; <u>Fig 6</u>	-	-	2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	printed circuit board mounted; minimum footprint	-	55	-	K/W



# **10. Characteristics**

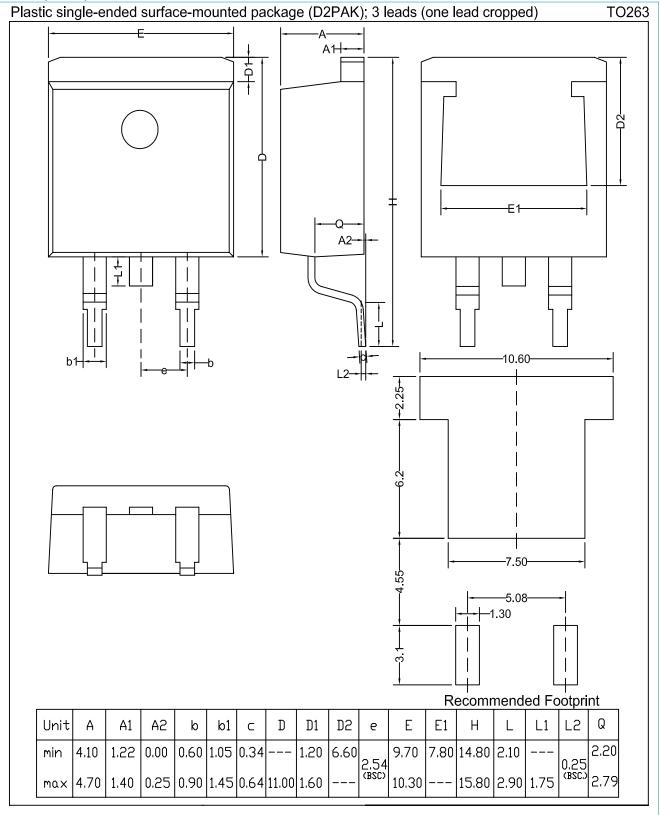
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	2	-	10	mA
		$V_{D} = 12 \text{ V}; \text{ I}_{T} = 0.1 \text{ A}; \text{ T2+ G-};$ T <sub>j</sub> = 25 °C; Fig. 7	2	-	10	mA
		$V_{D} = 12 \text{ V}; \text{ I}_{T} = 0.1 \text{ A}; \text{ T2- G-};$ T <sub>j</sub> = 25 °C; Fig. 7	2	-	10	mA
IL	latching current	V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	-	25	mA
		$V_{D}$ = 12 V; I <sub>G</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; Fig. 8	-	-	30	mA
		$V_{D}$ = 12 V; I <sub>G</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; Fig. 8	-	-	35	mA
I <sub>H</sub>	holding current			-	15	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.6	V
$V_{\rm GT}$	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A;T <sub>j</sub> = 25 °C; Fig. 11	-	0.8	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A;T <sub>j</sub> = 125 °C; Fig. 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics			,		
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit	500	-	-	V/µs
dI <sub>com</sub> /dt	rate of change of commutating current	$V_D = 400 \text{ V}; \text{ T}_j = 125 \text{ °C}; \text{ I}_{T(RMS)} = 12 \text{ A};$ $dV_{com}/dt = 20 \text{ V}/\mu\text{s}; \text{ (snubberless condition); gate open circuit}$	20	-	-	A/ms
		$V_D$ = 400 V; T <sub>j</sub> = 125 °C; I <sub>T(RMS)</sub> = 12 A; dV <sub>com</sub> /dt = 10 V/µs; gate open circuit	6	-	-	A/ms
		$V_D$ = 400 V; T <sub>j</sub> = 125 °C; I <sub>T(RMS)</sub> = 12 A; dV <sub>com</sub> /dt = 1 V/µs; gate open circuit	10	-	-	A/ms

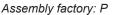


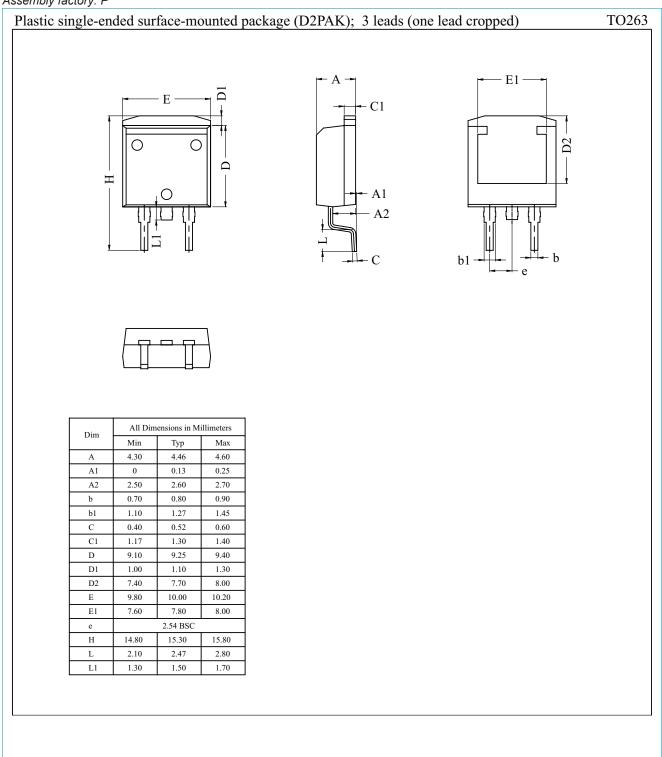


### **11. Package outline**

#### Assembly factory: N







# 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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